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# DATA SHEET

## **BFG591** NPN 7 GHz wideband transistor

Product specification  
Supersedes data of November 1992

1995 Sep 04



# NPN 7 GHz wideband transistor

# BFG591

### FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability.

### APPLICATIONS

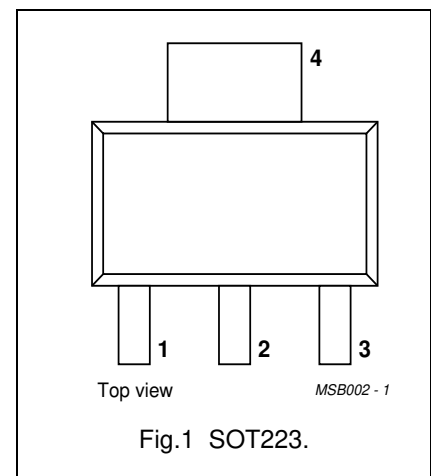
Intended for applications in the GHz range such as MATV or CATV amplifiers and RF communications subscriber equipment.

### DESCRIPTION

NPN silicon planar epitaxial transistor in a plastic, 4-pin SOT223 package.

### PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector



### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CB0}$	collector-base voltage	open emitter	–	–	20	V
$V_{CEO}$	collector-emitter voltage	open base	–	–	15	V
$I_C$	collector current (DC)		–	–	200	mA
$P_{tot}$	total power dissipation	up to $T_s = 80\text{ °C}$ ; note 1	–	–	2	W
$h_{FE}$	DC current gain	$I_C = 70\text{ mA}$ ; $V_{CE} = 8\text{ V}$	60	90	250	
$C_{re}$	feedback capacitance	$I_C = I_c = 0$ ; $V_{CE} = 12\text{ V}$ ; $f = 1\text{ MHz}$	–	0.7	–	pF
$f_T$	transition frequency	$I_C = 70\text{ mA}$ ; $V_{CE} = 12\text{ V}$ ; $f = 1\text{ GHz}$	–	7	–	GHz
$G_{UM}$	maximum unilateral power gain	$I_C = 70\text{ mA}$ ; $V_{CE} = 12\text{ V}$ ; $f = 900\text{ MHz}$ ; $T_{amb} = 25\text{ °C}$	–	13	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 70\text{ mA}$ ; $V_{CE} = 12\text{ V}$ ; $f = 900\text{ MHz}$ ; $T_{amb} = 25\text{ °C}$	–	12	–	dB

### Note

1.  $T_s$  is the temperature at the soldering point of the collector pin.

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	20	V
$V_{CEO}$	collector-emitter voltage	open base	–	15	V
$V_{EBO}$	emitter-base voltage	open collector	–	3	V
$I_C$	collector current (DC)		–	200	mA
$P_{tot}$	total power dissipation	up to $T_s = 80\text{ °C}$ ; note 1	–	2	W
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	note 1	35	K/W

**Note to the Limiting values and Thermal characteristics**

- $T_s$  is the temperature at the soldering point of the collector pin.

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**CHARACTERISTICS** $T_j = 25\text{ °C}$  (unless otherwise specified).

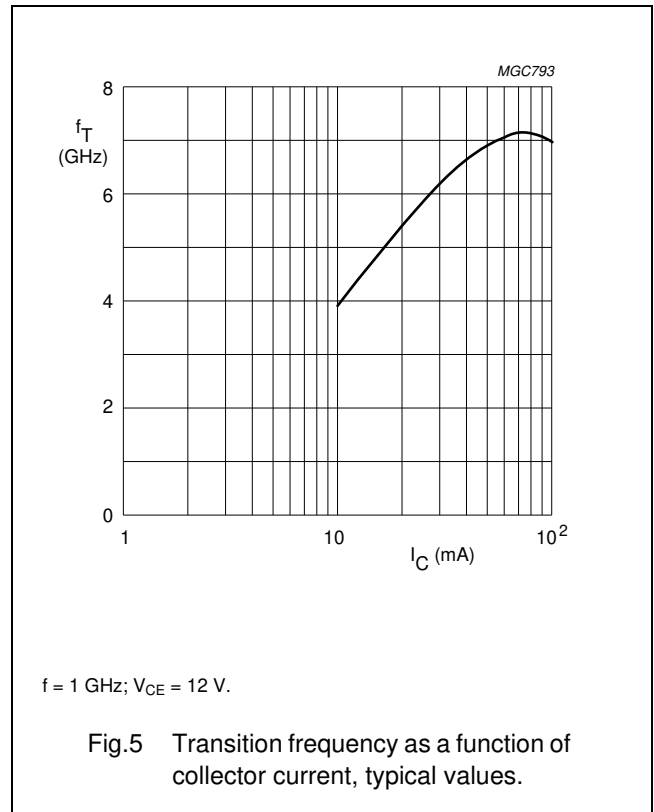
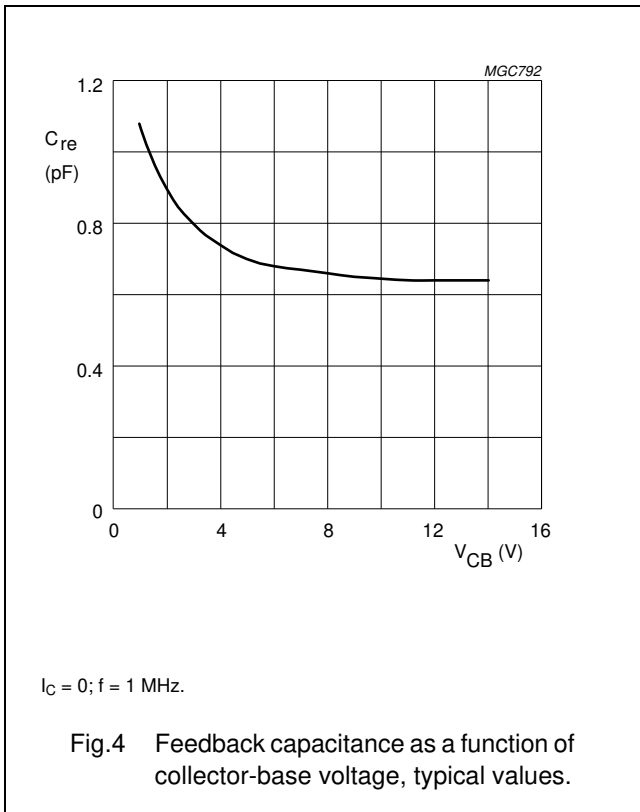
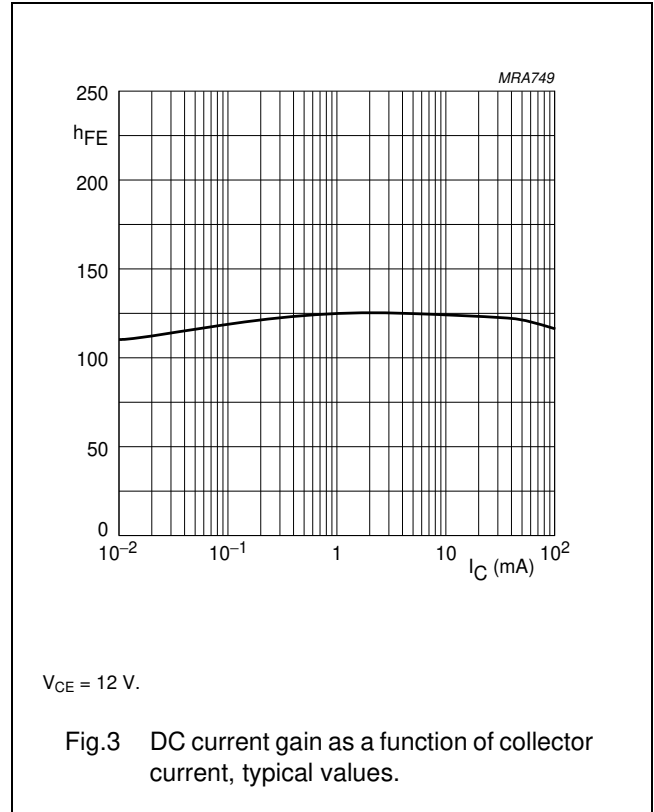
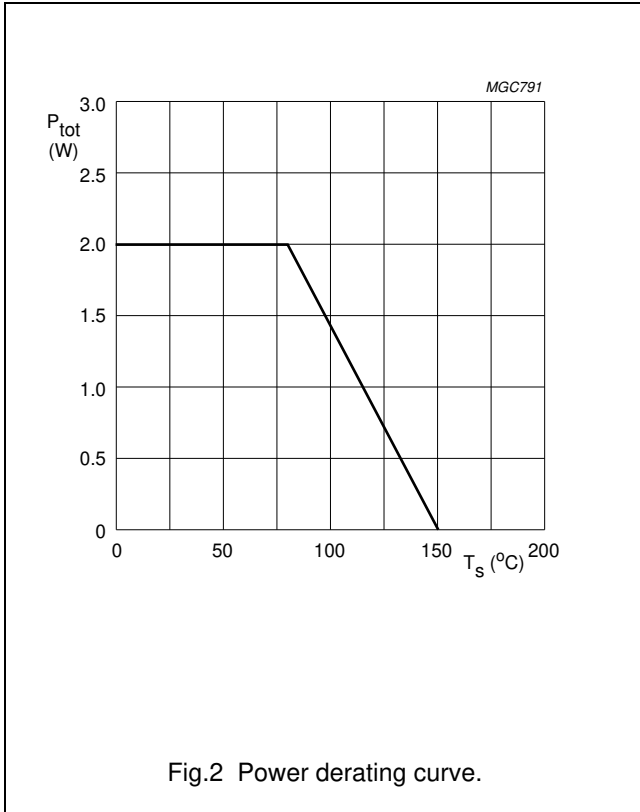
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 0.1\text{ mA}; I_E = 0$	20	–	–	V
$V_{(BR)CES}$	collector-emitter breakdown voltage	$I_C = 10\text{ mA}; I_B = 0$	15	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 0.1\text{ mA}; I_C = 0$	3	–	–	V
$I_{CBO}$	collector-base leakage current	$I_E = 0; V_{CB} = 10\text{ V}$	–	–	100	nA
$h_{FE}$	DC current gain	$I_C = 70\text{ mA}; V_{CE} = 8\text{ V}$	60	90	250	
$C_{re}$	feedback capacitance	$I_B = I_b = 0; V_{CE} = 12\text{ V};$ $f = 1\text{ MHz}$	–	0.7	–	pF
$f_T$	transition frequency	$I_C = 70\text{ mA}; V_{CE} = 12\text{ V};$ $f = 1\text{ GHz}$	–	7	–	GHz
$G_{UM}$	maximum unilateral power gain; note 1	$I_C = 70\text{ mA}; V_{CE} = 12\text{ V};$ $f = 900\text{ MHz}; T_{amb} = 25\text{ °C}$	–	13	–	dB
		$I_C = 70\text{ mA}; V_{CE} = 12\text{ V};$ $f = 2\text{ GHz}; T_{amb} = 25\text{ °C}$	–	7.5	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 70\text{ mA}; V_{CE} = 12\text{ V};$ $f = 1\text{ GHz}; T_{amb} = 25\text{ °C}$	–	12	–	dB
$V_o$	output voltage	note 2	–	700	–	mV

**Notes**

- $G_{UM}$  is the maximum unilateral power gain, assuming  $s_{12}$  is zero.  $G_{UM} = 10 \log \frac{|s_{21}|^2}{(1 - |s_{11}|^2)(1 - |s_{22}|^2)}$  dB.
- $d_{im} = 60\text{ dB}$  (DIN45004B);  
 $V_p = V_o$ ;  $V_q = V_o - 6\text{ dB}$ ;  $V_r = V_o - 6\text{ dB}$ ;  
 $f_p = 795.25\text{ MHz}$ ;  $f_q = 803.25\text{ MHz}$ ;  $f_r = 803.25\text{ MHz}$ ; measured at  $f_{(p+q-r)} = 793.25\text{ MHz}$ .

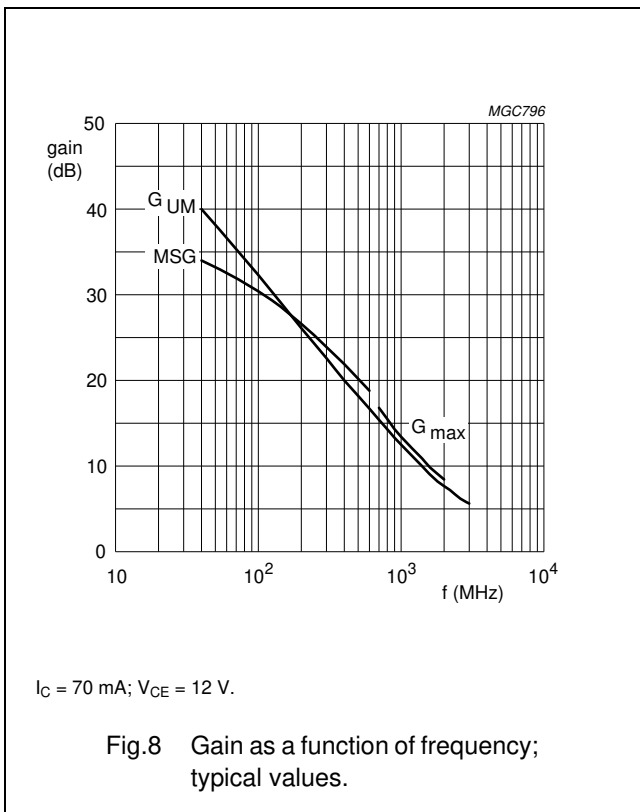
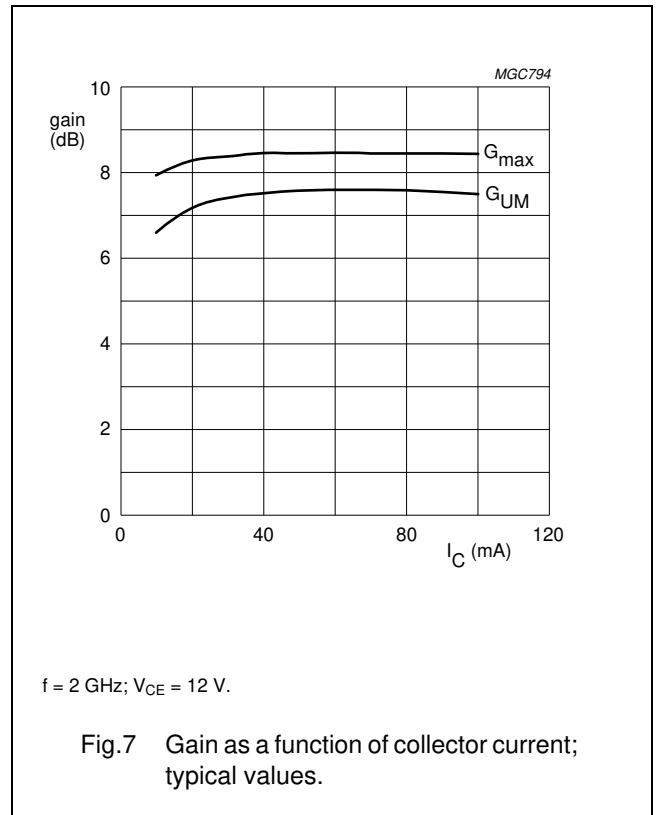
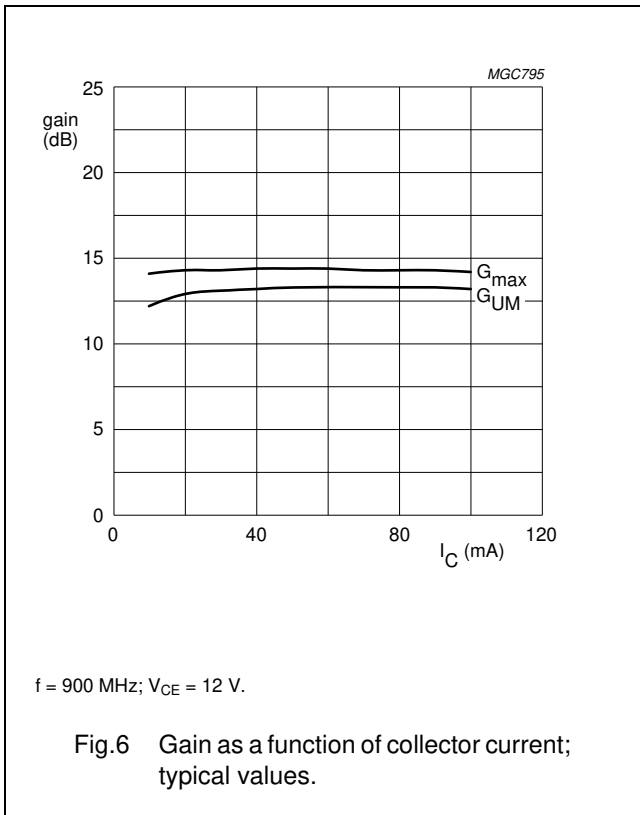
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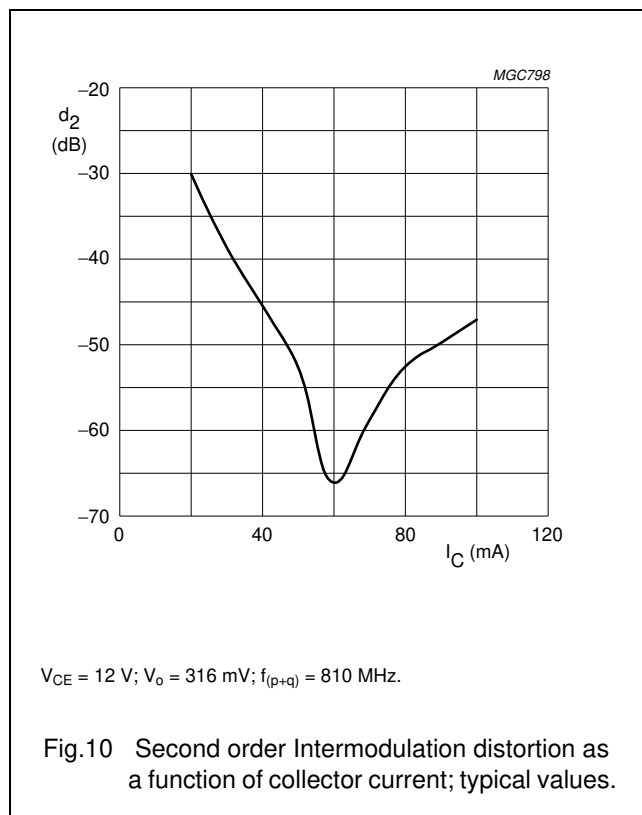
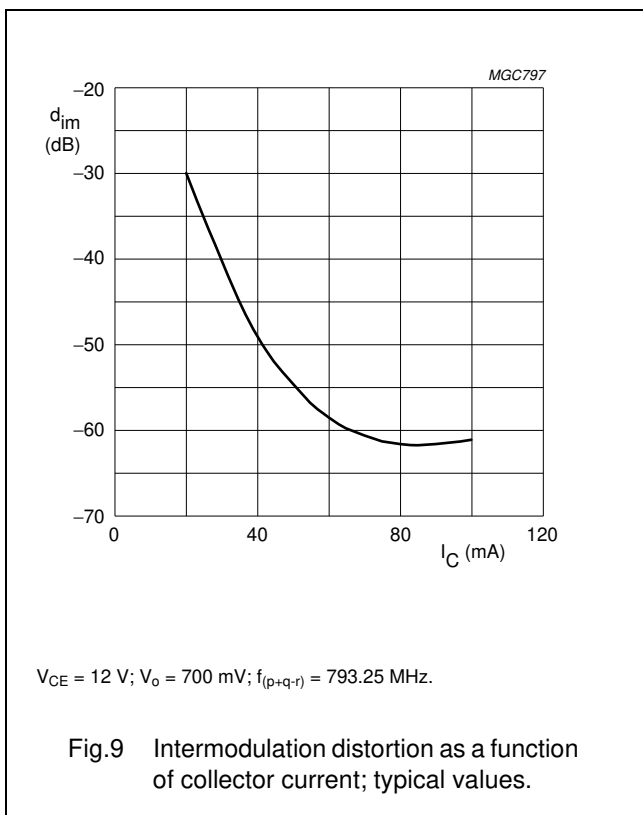
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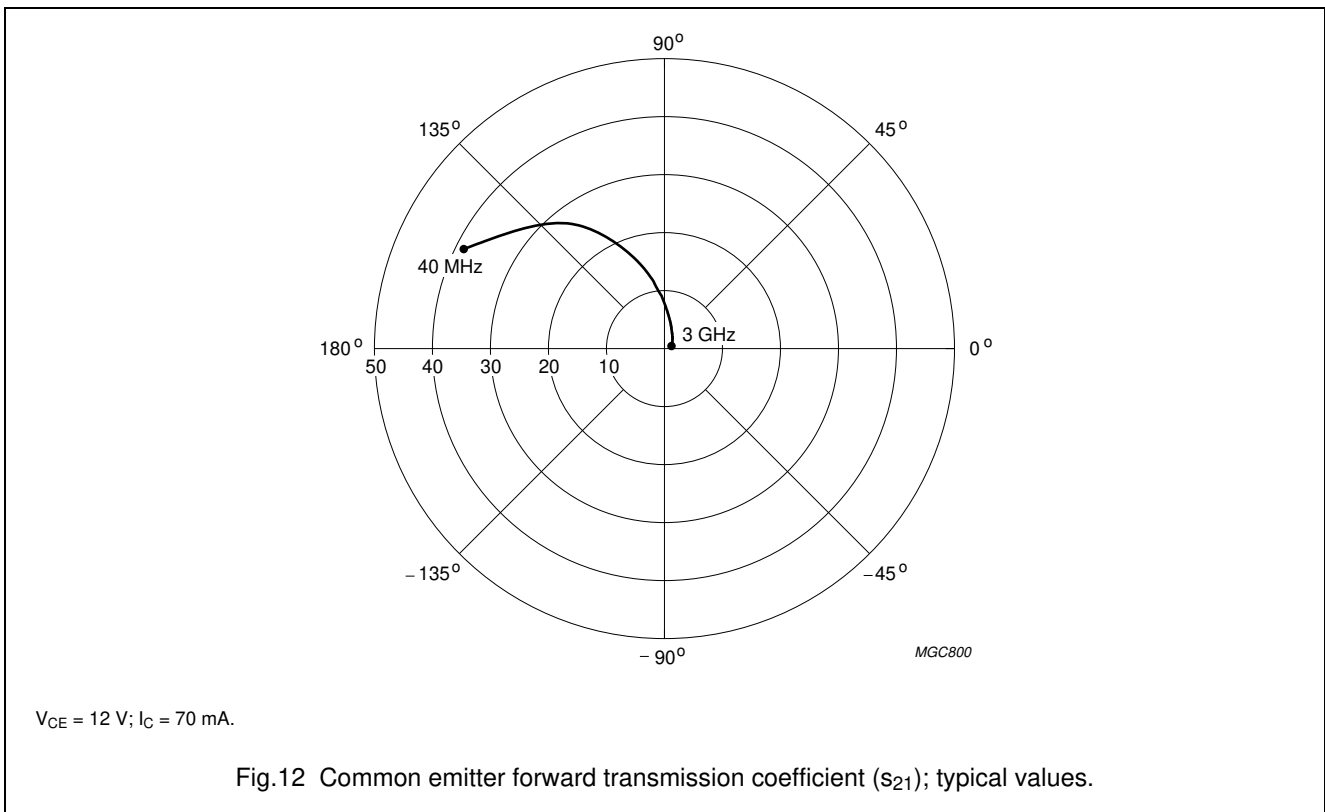
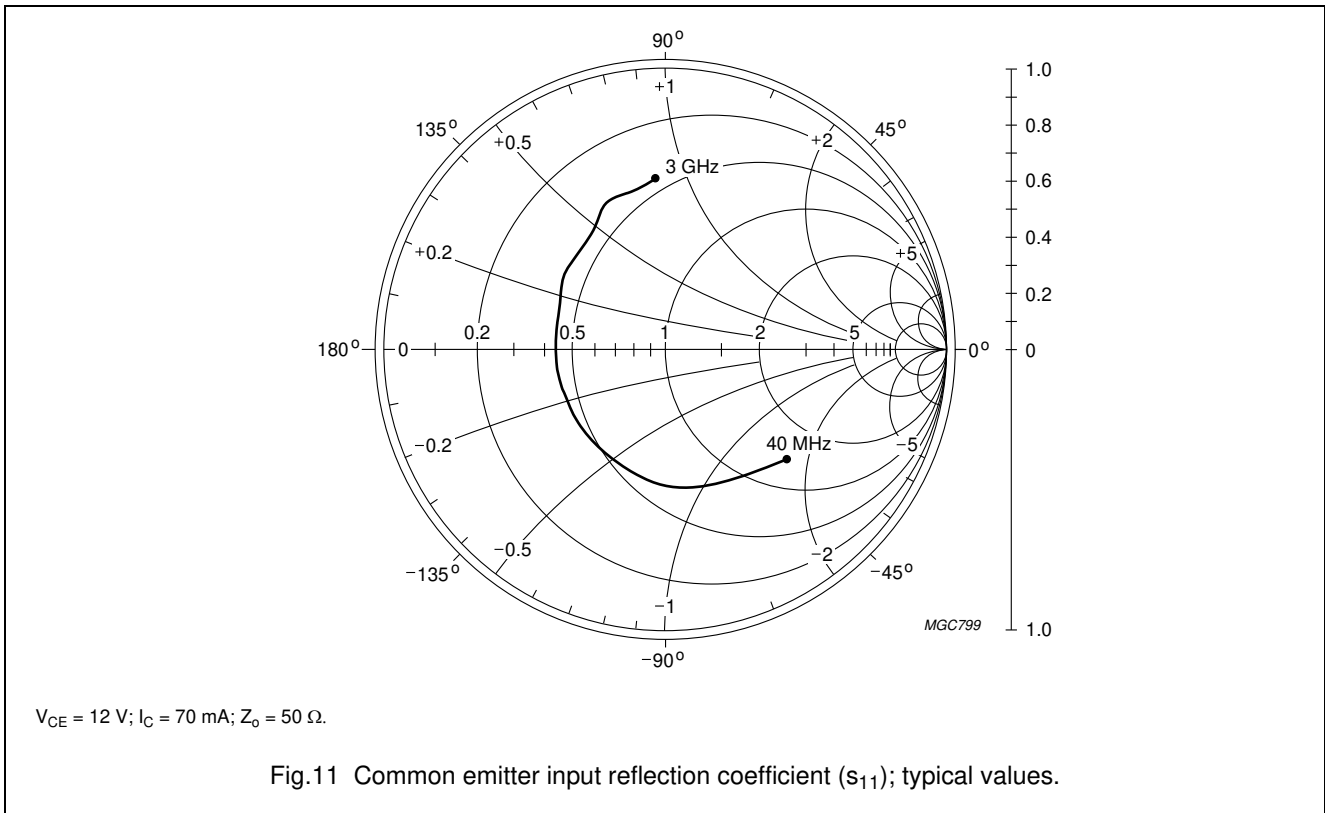
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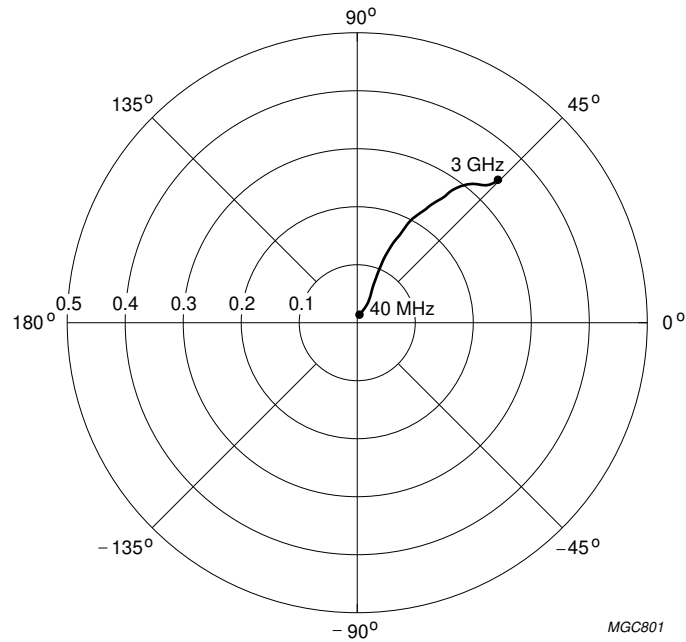
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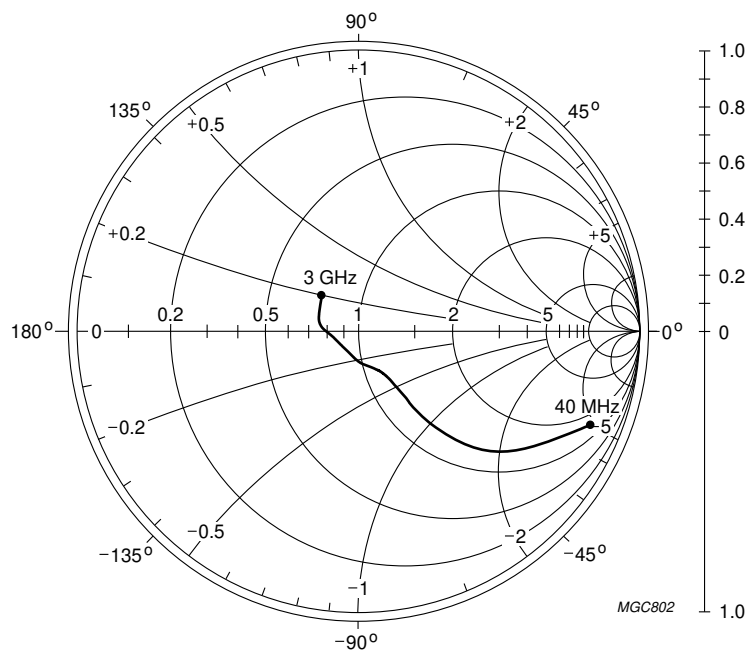
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$V_{CE} = 12\text{ V}; I_C = 70\text{ mA}$ .

Fig.13 Common emitter reverse transmission coefficient ( $s_{12}$ ); typical values.



$V_{CE} = 12\text{ V}; I_C = 70\text{ mA}; Z_o = 50\ \Omega$ .

Fig.14 Common emitter output reflection coefficient ( $s_{22}$ ); typical values.

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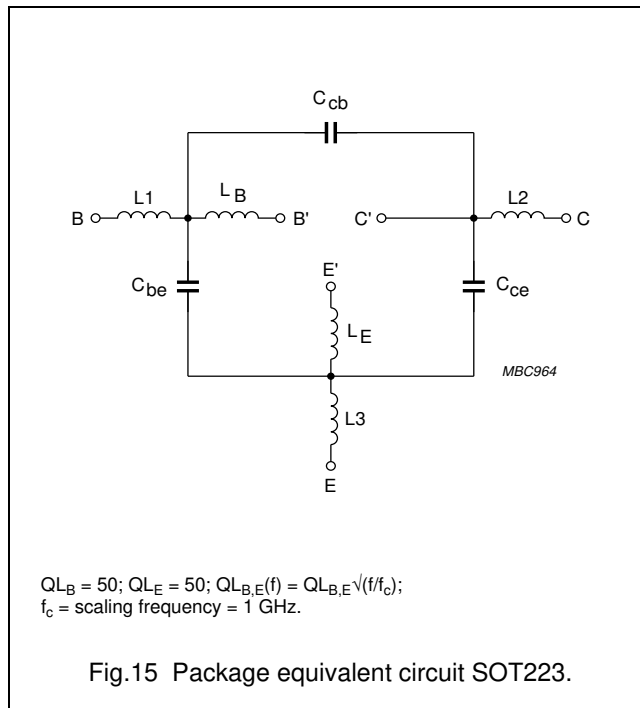
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SPICE parameters for the BFG591 crystal

SEQUENCE No.	PARAMETER	VALUE	UNIT
1	IS	1.341	fA
2	BF	123.5	–
3	NF	.988	m
4	VAF	75.85	V
5	IKF	9.656	A
6	ISE	232.2	fA
7	NE	2.134	–
8	BR	10.22	–
9	NR	1.016	–
10	VAR	1.992	V
11	IKR	294.1	mA
12	ISC	211.0	aA
13	NC	997.2	–
14	RB	5.00	Ω
15	IRB	1.000	μA
16	RBM	5.00	Ω
17	RE	1.275	Ω
18	RC	920.6	mΩ
19 (1)	XTB	0.000	–
20 (1)	EG	1.110	EV
21 (1)	XTI	3.000	–
22	CJE	3.821	pF
23	VJE	600.0	mV
24	MJE	348.5	m
25	TF	13.60	ps
26	XTF	71.73	–
27	VTF	10.28	V
28	ITF	1.929	A
29	PTF	0.000	deg
30	CJC	1.409	pF
31	VJC	219.4	mV
32	MJC	166.5	m
33	XCJ	2.340	m
34	TR	543.7	ns
35 (1)	CJS	0.000	F
36 (1)	VJS	750.0	mV
37 (1)	MJS	0.000	–
38	FC	733.2	m

Note

1. These parameters have not been extracted, the default values are shown.



List of components (see Fig.15)

DESIGNATION	VALUE	UNIT
C <sub>be</sub>	182	fF
C <sub>cb</sub>	16	fF
C <sub>ce</sub>	249	fF
L1	0.025	nH
L2	1.19	nH
L3	0.60	nH
L <sub>B</sub>	1.50	nH
L <sub>E</sub>	0.50	nH

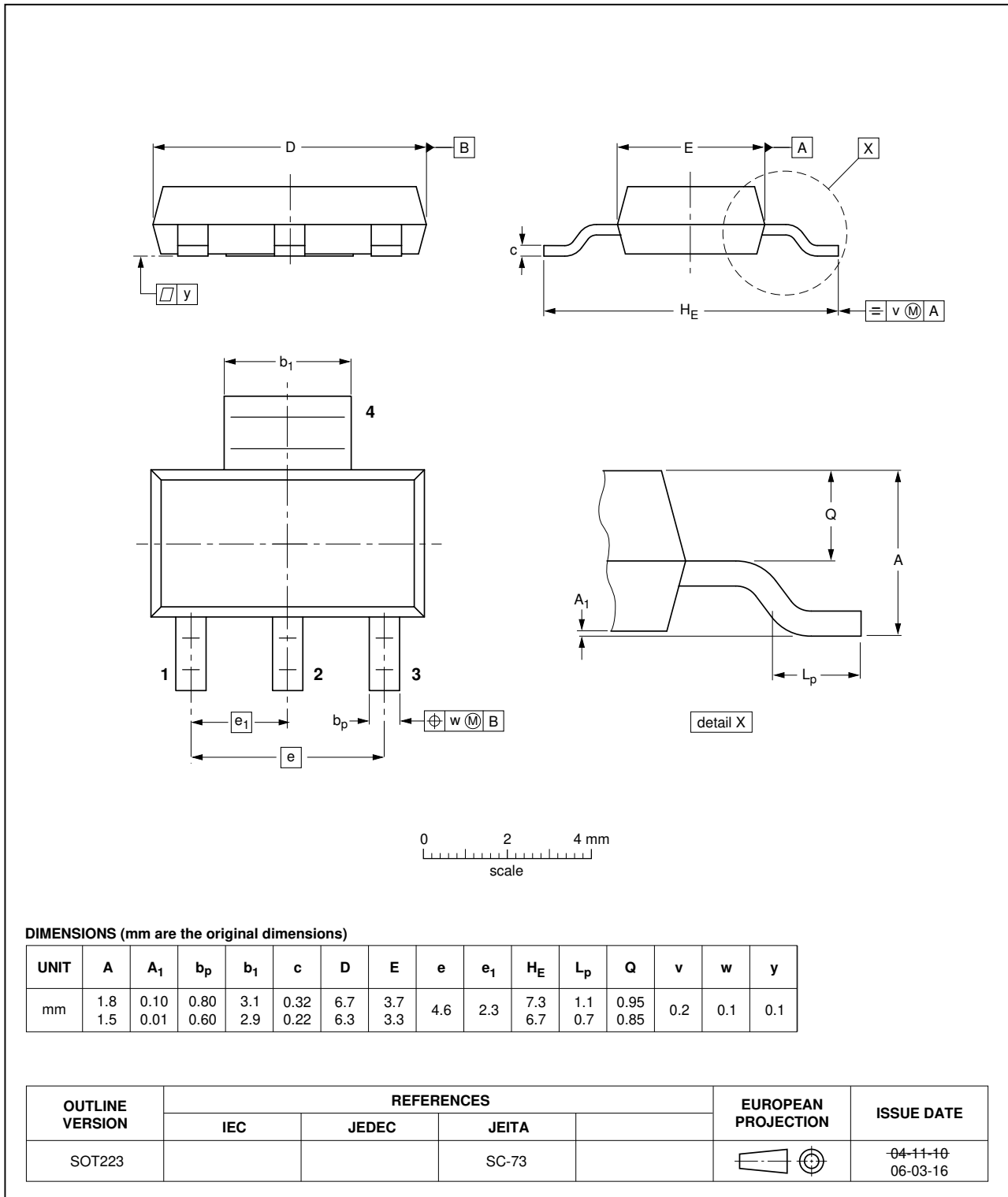
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PACKAGE OUTLINE

Plastic surface-mounted package with increased heatsink; 4 leads

SOT223



## NPN 7 GHz wideband transistor

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## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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